

INCHANGE SEMICONDUCTOR

isc Silicon NPN Power Transistor

2SC1008

DESCRIPTION

- NPN high-voltage transistor
- Low current (max. 700 mA)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

 Designed for Switching and amplification in high voltage applications, such as telephony applications.

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	8	V
lc	Collector Current-Continuous	0.7	A
Pc	Collector Power Dissipation @ $T_a < 50^{\circ}C$	0.8	W
J	Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)



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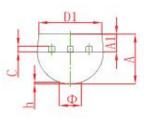
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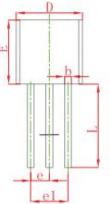
ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
Collector-Emitter Saturation Voltage	I _C = 500mA; I _B = 50mA			0.4	V
Base-Emitter Saturation Voltage	I _C = 500mA; I _B = 50mA			1.1	V
Collector Cutoff Current	V _{CB} = 60V; I _E = 0			0.1	uA
Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			0.1	uA
DC Current Gain	I _C =50mA ; V _{CE} = 2V	40		400	
-	Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage Collector Cutoff Current Emitter Cutoff Current	Collector-Emitter Saturation Voltage $I_C = 500$ mA; $I_B = 50$ mABase-Emitter Saturation Voltage $I_C = 500$ mA; $I_B = 50$ mACollector Cutoff Current $V_{CB} = 60$ V; $I_E = 0$ Emitter Cutoff Current $V_{EB} = 5$ V; $I_C = 0$	Collector-Emitter Saturation Voltage $I_C = 500 \text{mA}; I_B = 50 \text{mA}$ Base-Emitter Saturation Voltage $I_C = 500 \text{mA}; I_B = 50 \text{mA}$ Collector Cutoff Current $V_{CB} = 60 \text{V}; I_E = 0$ Emitter Cutoff Current $V_{EB} = 5 \text{V}; I_C = 0$	Collector-Emitter Saturation Voltage $I_C = 500 \text{mA}; I_B = 50 \text{mA}$ Base-Emitter Saturation Voltage $I_C = 500 \text{mA}; I_B = 50 \text{mA}$ Collector Cutoff Current $V_{CB} = 60V; I_E = 0$ Emitter Cutoff Current $V_{EB} = 5V; I_C = 0$	Collector-Emitter Saturation Voltage $I_C = 500$ mA; $I_B = 50$ mA0.4Base-Emitter Saturation Voltage $I_C = 500$ mA; $I_B = 50$ mA1.1Collector Cutoff Current $V_{CB} = 60$ V; $I_E = 0$ 0.1Emitter Cutoff Current $V_{EB} = 5$ V; $I_C = 0$ 0.1

TO-92 Package Outline Dimensions





Combal	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
C	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
0	1.270 TYP		0.050 TYP	TYP
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015



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